

TURBO 2 ULTRAFAST HIGH VOLTAGE RECTIFIER
Table 1: Main Product Characteristics

$I_{F(AV)}$	1 A
V_{RRM}	600 V
I_R (max)	75 μA
T_j	175°C
V_F (typ)	1.0 V
t_{rr} (max)	25 ns

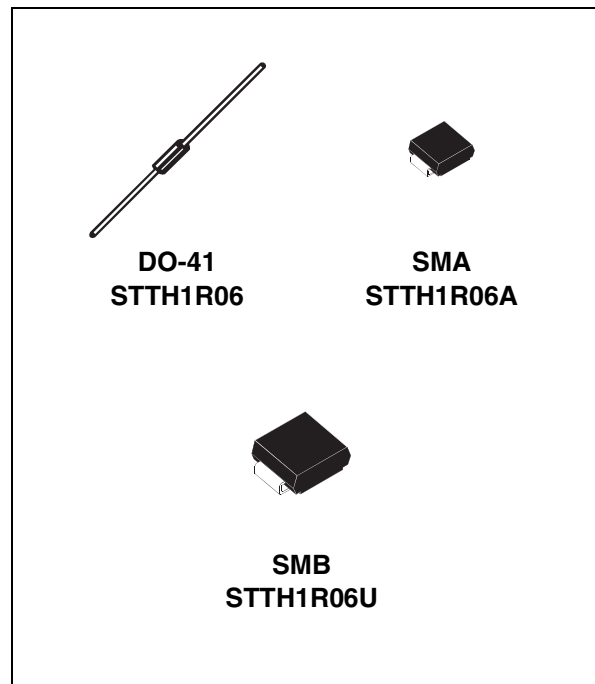
FEATURES AND BENEFITS

- Ultrafast switching
- Low reverse recovery current
- Low thermal resistance
- Reduces switching & conduction losses

DESCRIPTION

The STTH1R06, which is using ST Turbo 2 600V technology, is specially suited as boost diode in power factor correction circuitry.

The device is also intended for use as a free wheeling diode in power supplies and other power switching applications.


Table 2: Order Codes

Part Number	Marking
STTH1R06	STTH1R06
STTH1R06RL	STTH1R06

Part Number	Marking
STTH1R06A	HR6
STTH1R06U	BR6

Table 3: Absolute Ratings (limiting values)

Symbol	Parameter		Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		600	V	
$I_{F(RMS)}$	RMS forward voltage	DO-41	10	A	
		SMA / SMB	7		
$I_{F(AV)}$	Average forward current	DO-41	$T_c = 100^\circ\text{C}$ $\delta = 0.5$	1	A
		SMA	$T_c = 125^\circ\text{C}$ $\delta = 0.5$		
		SMB	$T_c = 135^\circ\text{C}$ $\delta = 0.5$		
I_{FSM}	Surge non repetitive forward current	DO-41	$t_p = 10\text{ms}$ sinusoidal	25	A
		SMA / SMB		20	
T_{stg}	Storage temperature range		-65 to + 175	°C	
T_j	Maximum operating junction temperature		175	°C	

Table 4: Thermal Resistance

Symbol	Parameter			Value (max).	Unit
$R_{th(j-l)}$	Junction to lead	L = 10mm	DO-41	45	°C/W
			SMA	30	
			SMB	25	
$R_{th(j-a)}$	Junction to ambient ⁽¹⁾	L = 10mm	DO-41	70	°C/W

Note 1: $R_{th(j-a)}$ is measured with a copper area $S = Scm^2$ (see figure12).

Table 5: Static Electrical Characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
I_R	Reverse leakage current	$T_j = 25^\circ C$	$V_R = V_{RRM}$			1	μA
		$T_j = 150^\circ C$			10	75	
V_F	Forward voltage drop	$T_j = 25^\circ C$	$I_F = 1A$			1.7	V
		$T_j = 150^\circ C$			1.0	1.25	

To evaluate the conduction losses use the following equation: $P = 1.03 \times I_{F(AV)} + 0.27 I_F^2(RMS)$

Table 6: Dynamic Characteristics

Symbol	Parameter	Test conditions		Min.	Typ	Max.	Unit
t_{rr}	Reverse recovery time	$T_j = 25^\circ C$	$I_F = 0.5A$ $I_{rr} = 0.25A$ $I_R = 1A$			25	ns
			$I_F = 1A$ $di_F/dt = -50 A/\mu s$ $V_R = 30V$		30	45	
t_{fr}	Forward recovery time	$T_j = 25^\circ C$	$I_F = 1A$ $di_F/dt = 100 A/\mu s$ $V_{FR} = 1.1 \times V_{Fmax}$			100	ns
V_{FR}	Forward recovery voltage	$T_j = 25^\circ C$	$I_F = 1A$ $di_F/dt = 100 A/\mu s$ $V_{FR} = 1.1 \times V_{Fmax}$			10	V

Figure 1: Conduction losses versus average forward current

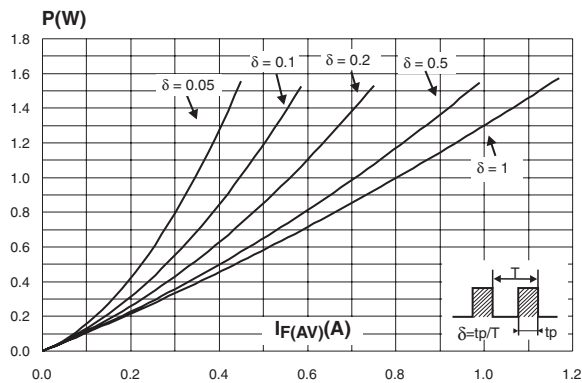


Figure 2: Forward voltage drop versus forward current

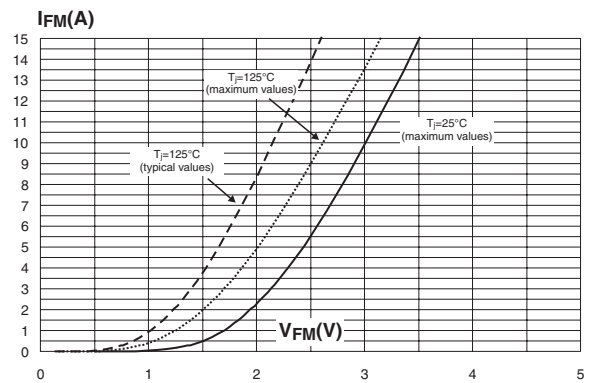


Figure 3: Relative variation of thermal impedance junction to case versus pulse duration (DO-41)

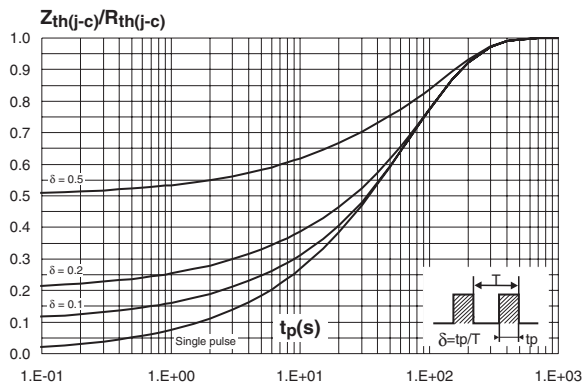


Figure 4: Relative variation of thermal impedance junction to case versus pulse duration (SMA)

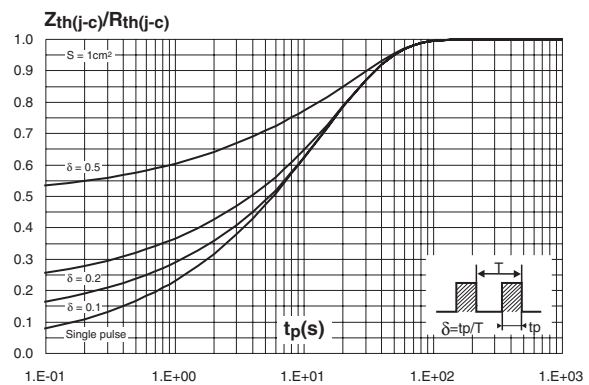


Figure 5: Relative variation of thermal impedance junction to case versus pulse duration (SMB)

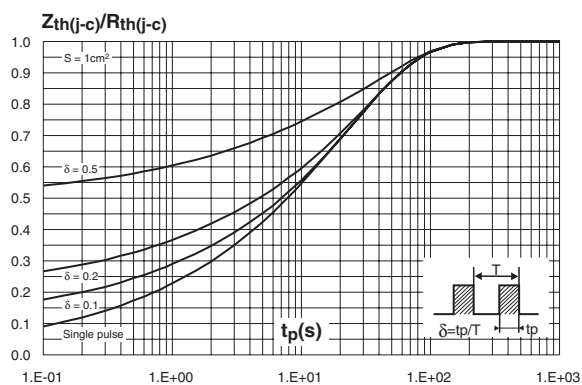


Figure 6: Peak reverse recovery current versus di_F/dt (typical values)

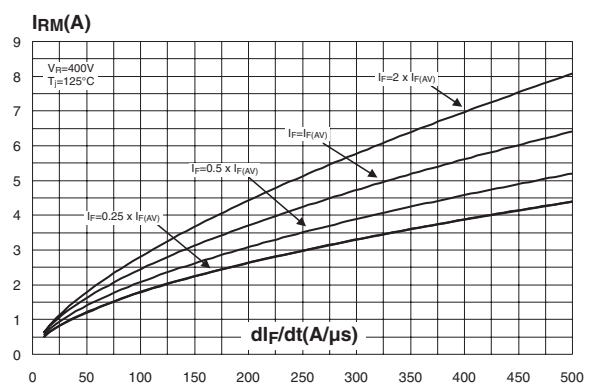


Figure 7: Reverse recovery time versus di_F/dt (typical values)

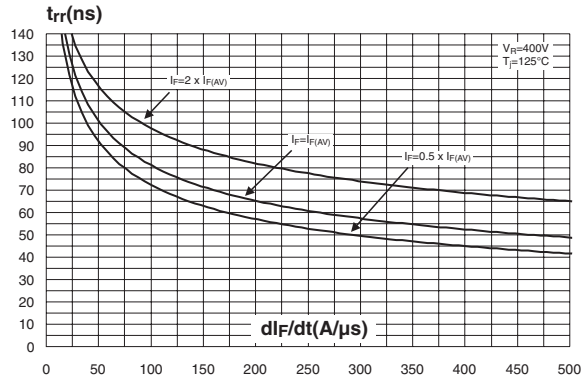


Figure 8: Reverse recovery charges versus di_F/dt (typical values)

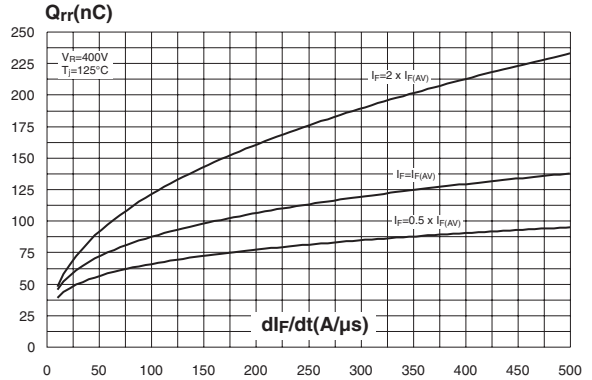


Figure 9: Reverse recovery softness factor versus di_F/dt (typical values)

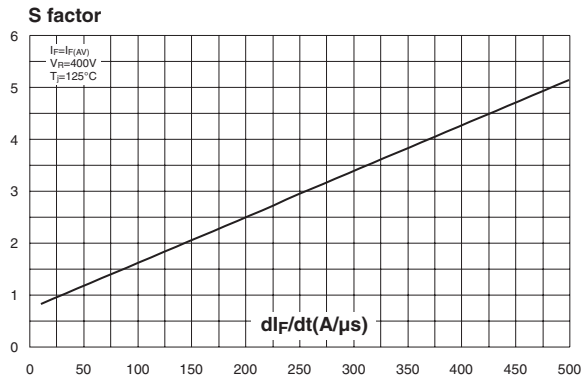


Figure 10: Relative variations of dynamic parameters versus junction temperature

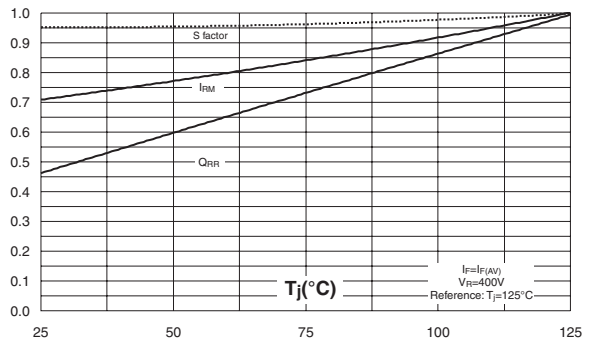


Figure 11: Transient peak forward voltage versus di_F/dt (typical values)

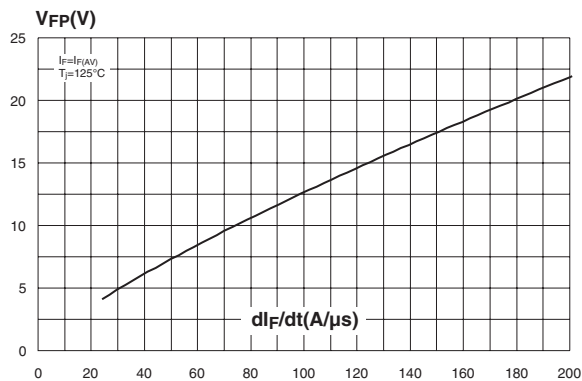


Figure 12: Forward recovery time versus di_F/dt (typical values)

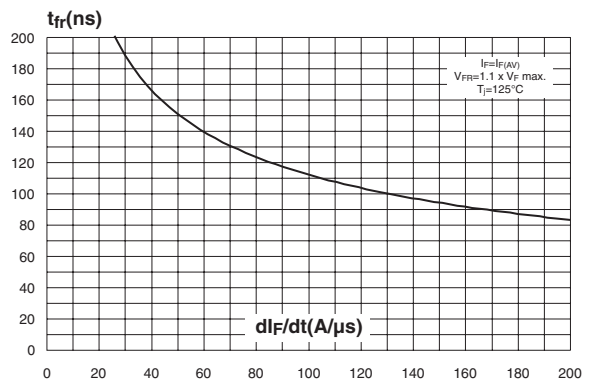


Figure 13: Junction capacitance versus reverse voltage applied (typical values)

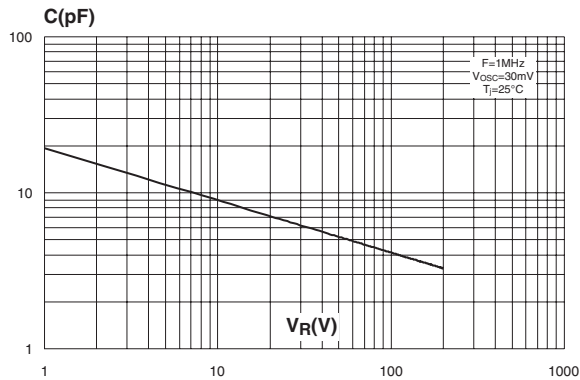


Figure 14: Thermal resistance junction to ambient versus copper surface under each lead (epoxy FR4, $e_{CU}=35\mu\text{m}$) (DO-41, SMB)

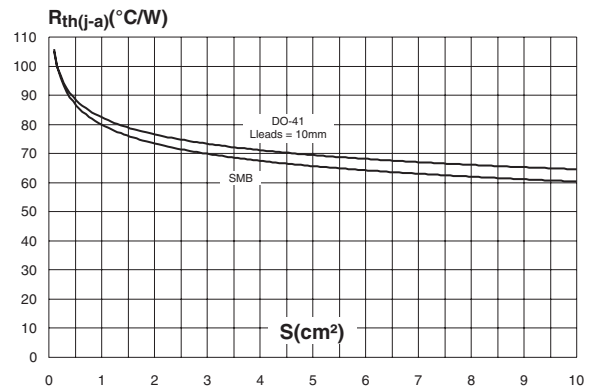


Figure 15: Thermal resistance junction to ambient versus copper surface under each lead (epoxy FR4, $e_{CU}=35\mu\text{m}$) (SMA)

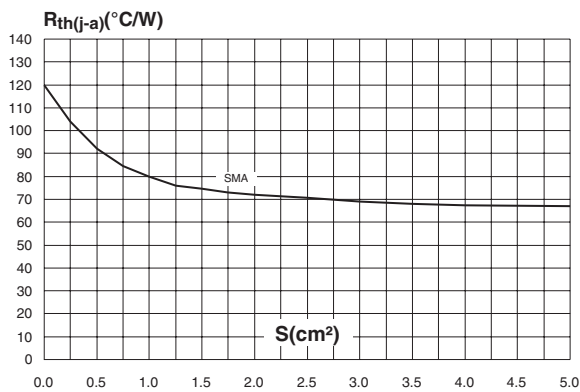


Figure 16: SMA Package Mechanical Data

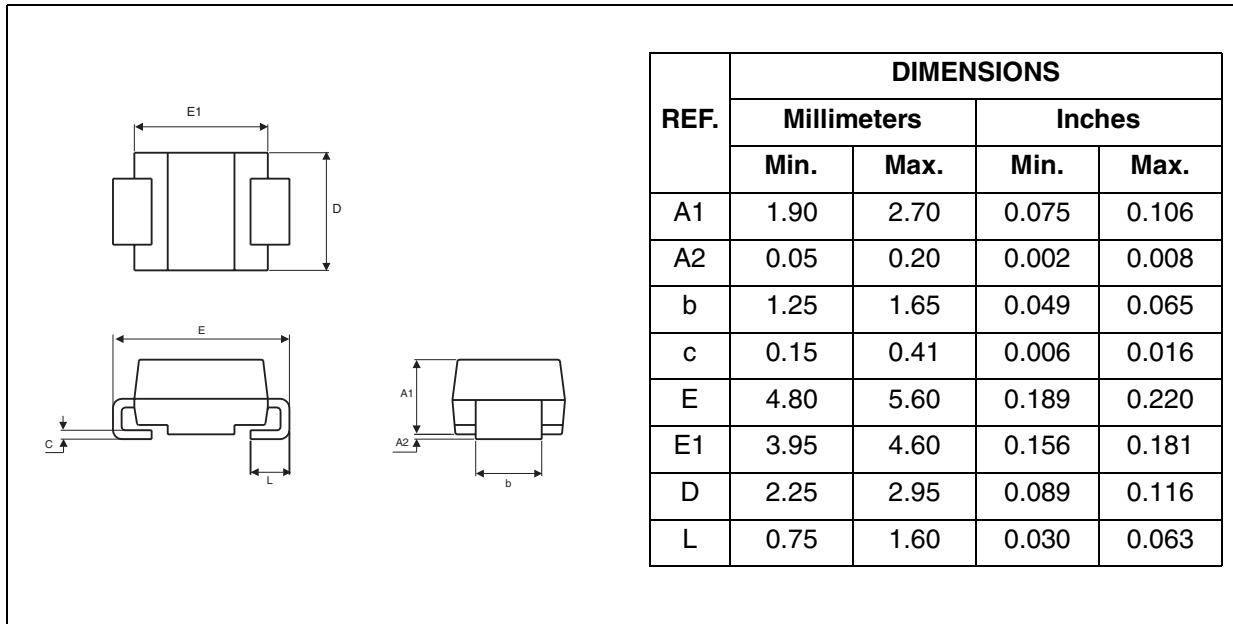


Figure 17: SMA Foot Print Dimensions (in millimeters)

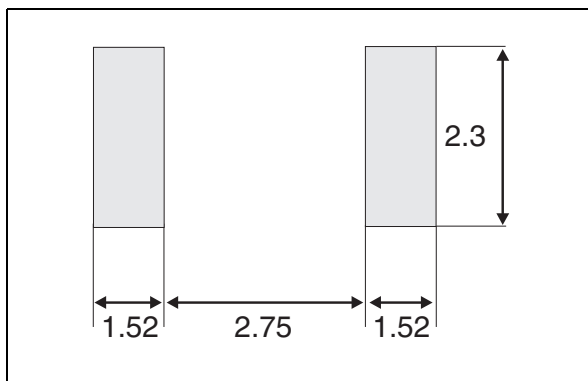


Figure 18: SMB Package Mechanical Data

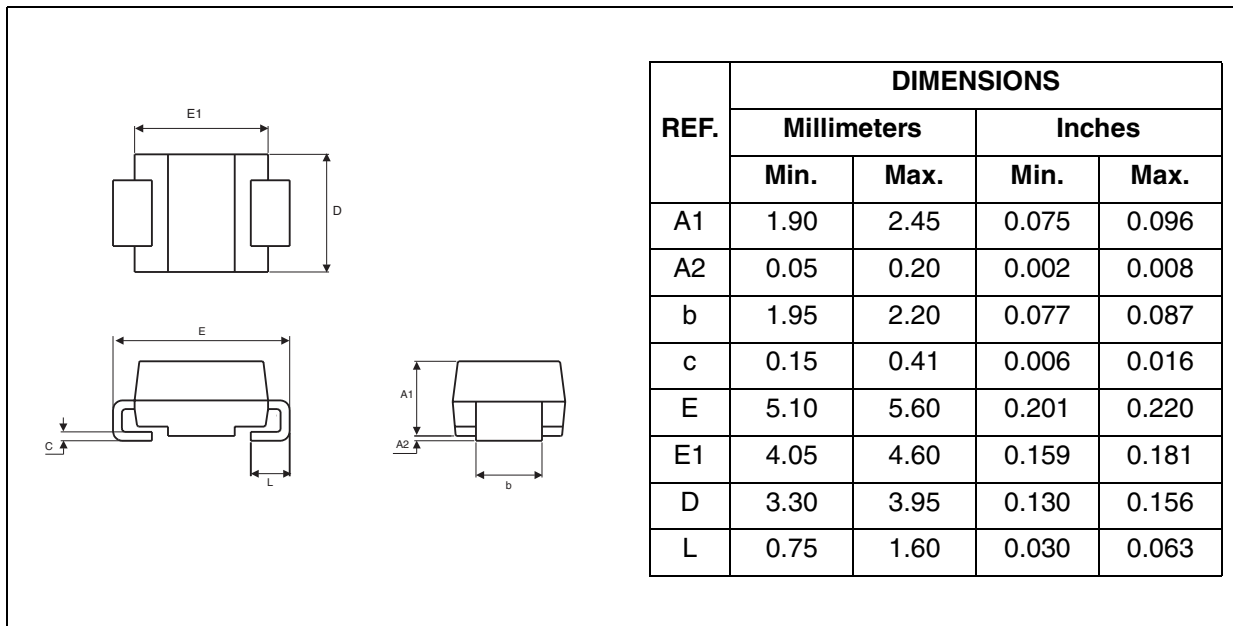


Figure 19: SMB Foot Print Dimensions
(in millimeters)

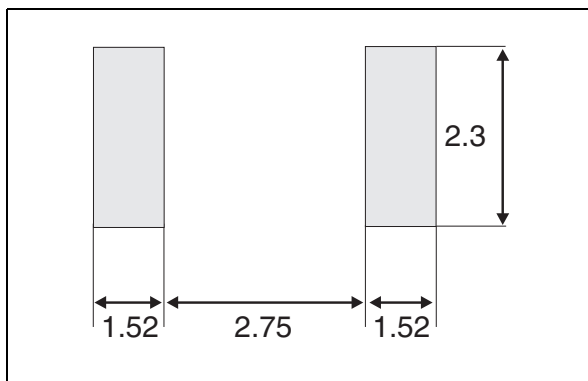


Figure 20: DO-41 Package Mechanical Data

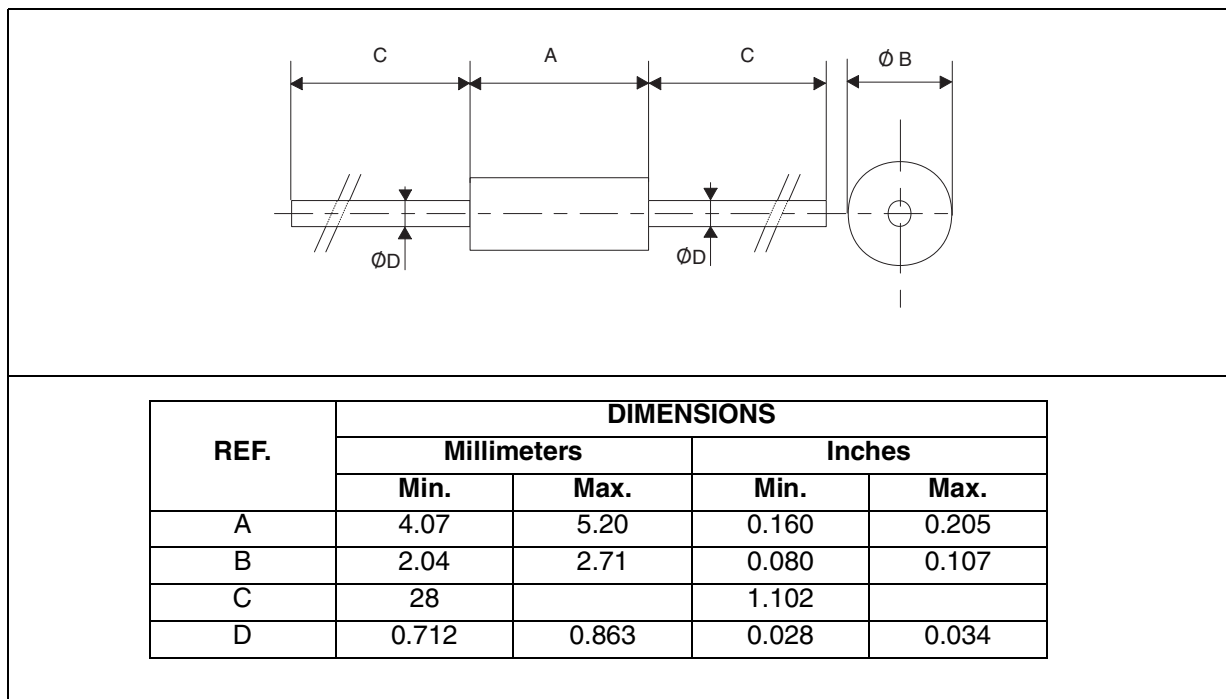


Table 7: Ordering Information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH1R06	STTH1R06	DO-41	0.34 g	2000	Ammopack
STTH1R06RL	STTH1R06	DO-41	0.34 g	5000	Tape & reel
STTH1R06A	AR6	SMA	0.068 g	5000	Tape & reel
STTH1R06B	BR6	SMB	0.11 g	2500	Tape & reel

- Epoxy meets UL94, V0

Table 8: Revision History

Date	Revision	Description of Changes
Apr-2003	1	First issue
07-Sep-2004	2	DO-41 and SMA packages added

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a registered trademark of STMicroelectronics.
All other names are the property of their respective owners

© 2004 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America
www.st.com

